

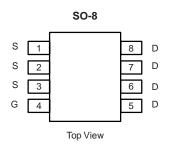
AP9578M-VB Datasheet P-Channel 60 V (D-S) MOSFET

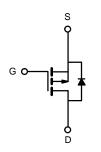
PRODUCT SUMMARY					
V _{DS} (V)	-60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.060				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.063				
I _D (A) per leg	-8				

FEATURES

- TrenchFET® power MOSFET
- 100 % R_g and UIS tested







P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	-60	V	
Gate-Source Voltage		V_{GS}	± 20	v I	
Continuous Drain Current	T _C = 25 °C	I-	-8		
	T _C = 125 °C	- I _D	-4.75		
Continuous Source Current (Diode Conduction)		I _S	-4.5	Α	
Pulsed Drain Current a		I _{DM}	-32		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	-22.4		
Single Pulse Avalanche Energy	L=0.1 MH	E _{AS}	25	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	- P _D	5	W	
	T _C = 125 °C		1.67	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount b	R_{thJA}	110	°C/W	
Junction-to-Foot (Drain)		R_{thJF}	30	C/VV	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•	•			!		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		-60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA		-1.0		-2.5	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = -60 V	=	-	-1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	
		V _{GS} = 0 V	V _{DS} = -60 V, T _J = 175 °C	-	-	-150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-30	-	-	Α
		V _{GS} = -10 V	I _D = -4.3 A	-	0.060	-	Ω
Duein Course On Chata Basistana 3	B	V _{GS} = -10 V	I _D = -4.3 A, T _J = 125 °C	-	0.070	-	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -4.3 A, T _J = 175 °C	-	0.080	-	
		$V_{GS} = -4.5 \text{ V}$	I _D = -3.8 A	-	0.063	-	
Forward Transconductance b	9fs	$V_{DS} = -15 \text{ V}, I_D = -4.3 \text{ A}$		-	13	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		= 0 V V _{DS} = -30 V, f = 1 MHz	=	1500	-	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	334	417	
Reverse Transfer Capacitance	C _{rss}			=	114	142	
Total Gate Charge ^c	Qg			-	43.4	65	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -30 \text{ V}, I_{D} = -5 \text{ A}$	=	4.7	=	nC
Gate-Drain Charge ^c	Q _{gd}			-	9	-	
Gate Resistance	R _g	f = 1 MHz		1.3	2.5	4	Ω
Turn-On Delay Time ^c	t _{d(on)}				11	17	
Rise Time ^c	t _r	$V_{DD} = -30 \text{ V}, R_L = 8.8 \Omega$ $I_D \cong -5 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		-	11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	35	52	
Fall Time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Chara	cteristics ^b	•					
Pulsed Current a	I _{SM}			-	-	-32	Α
Forward Voltage	V _{SD}	I _F = -2.8 A, V _{GS} = 0 V		_	-0.8	-1.2	V

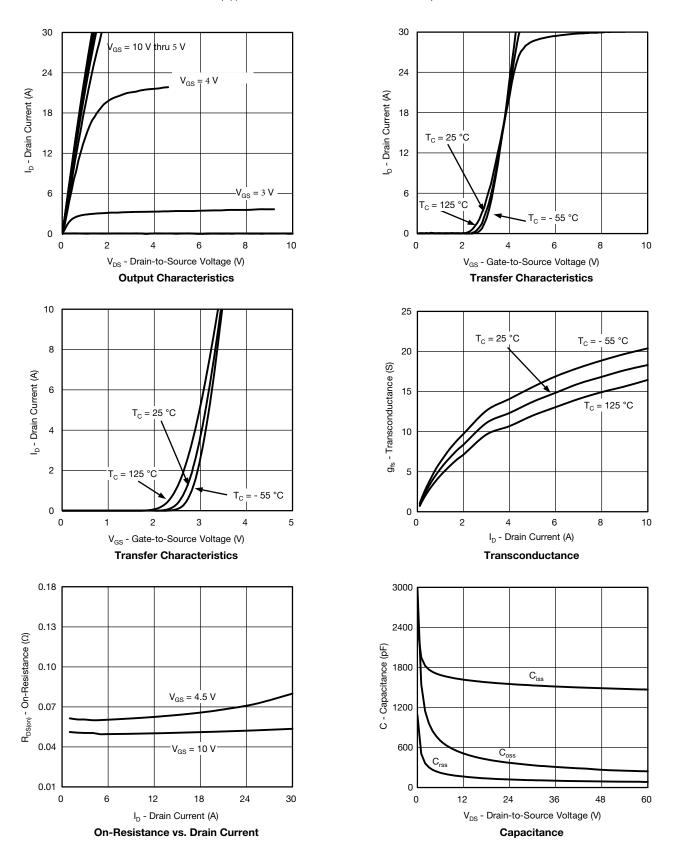
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

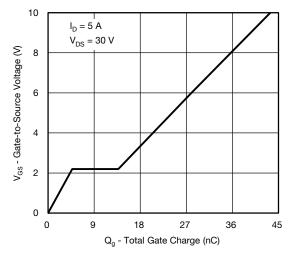


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

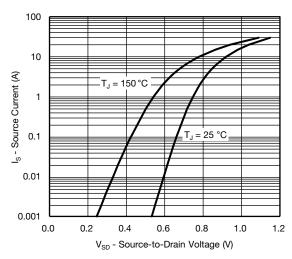




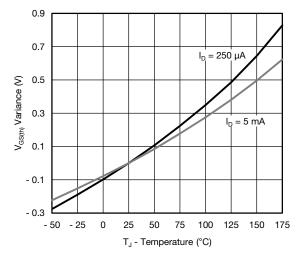
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



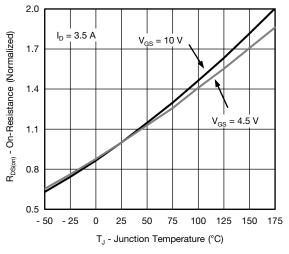
Gate Charge



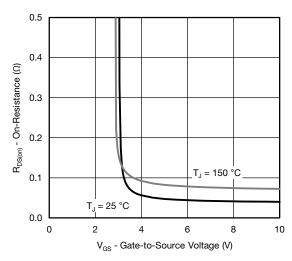
Source Drain Diode Forward Voltage



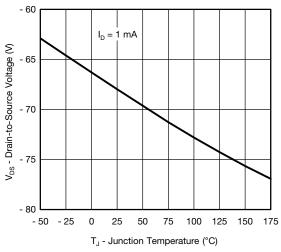
Threshold Voltage



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

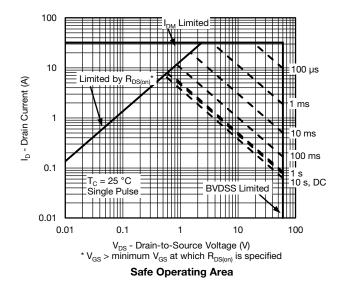


Drain Source Breakdown vs. Junction Temperature

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THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



2 Normalized Effective Transient Thermal Impedance Duty Cycle = 0.5 0.2 0.1 P_{DM} 0.05 t₁ 1. Duty Cycle, D = 0.02 2. Per Unit Base = R_{thJA} = 105 °C/W $3.\,T_{JM}\,-\,T_A=P_{DM}Z_{thJA}{}^{(t)}$ Single Pulse 4. Surface Mounted 0.01 10-3 10-4 10⁻² 10-1 10 100 600 Square Wave Pulse Duration (s)

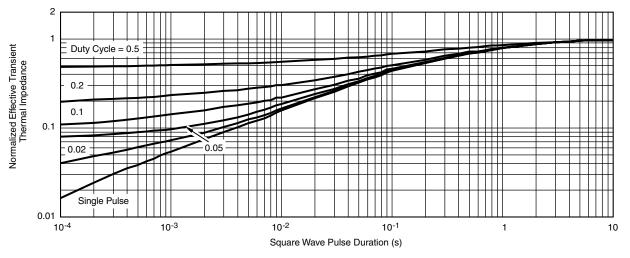
Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

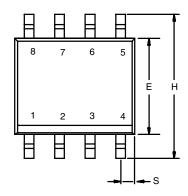
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

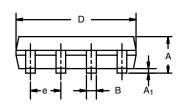
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

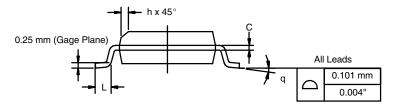
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIMETERS INCHE			HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. J. 11-Sep-06						

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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